

# Supporting Information

## **Aerosol Jet Printed p- and n-type Electrolyte Gated Transistors with a Variety of Electrode Materials: Exploring Practical Routes to Printed Electronics**

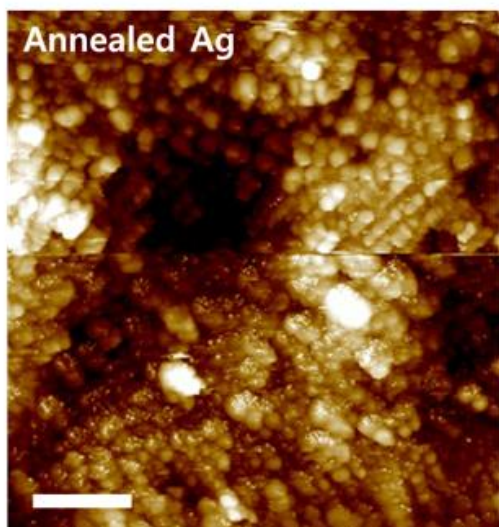
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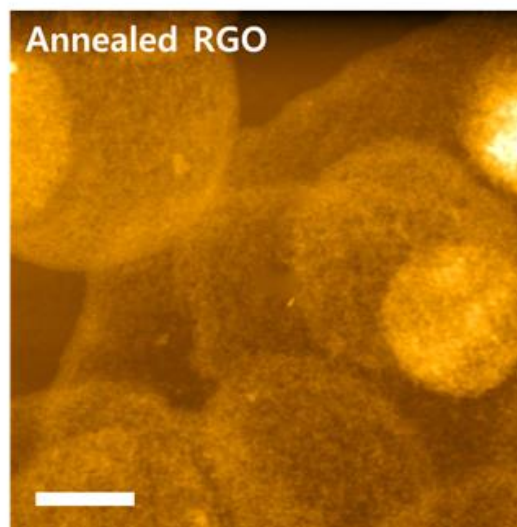
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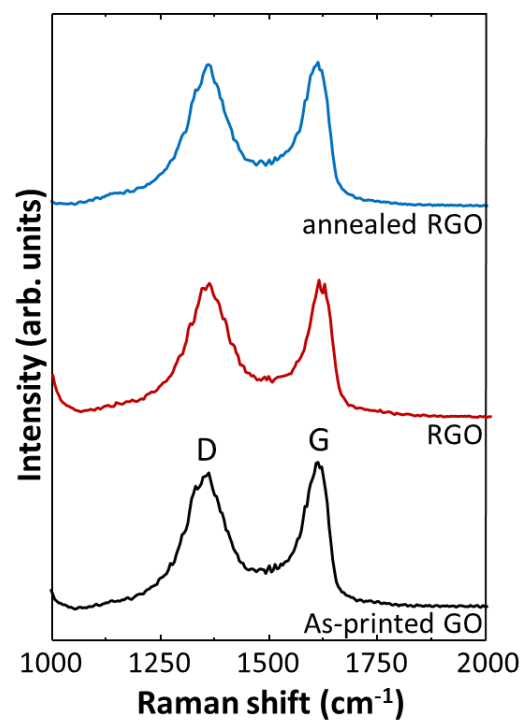
(a)



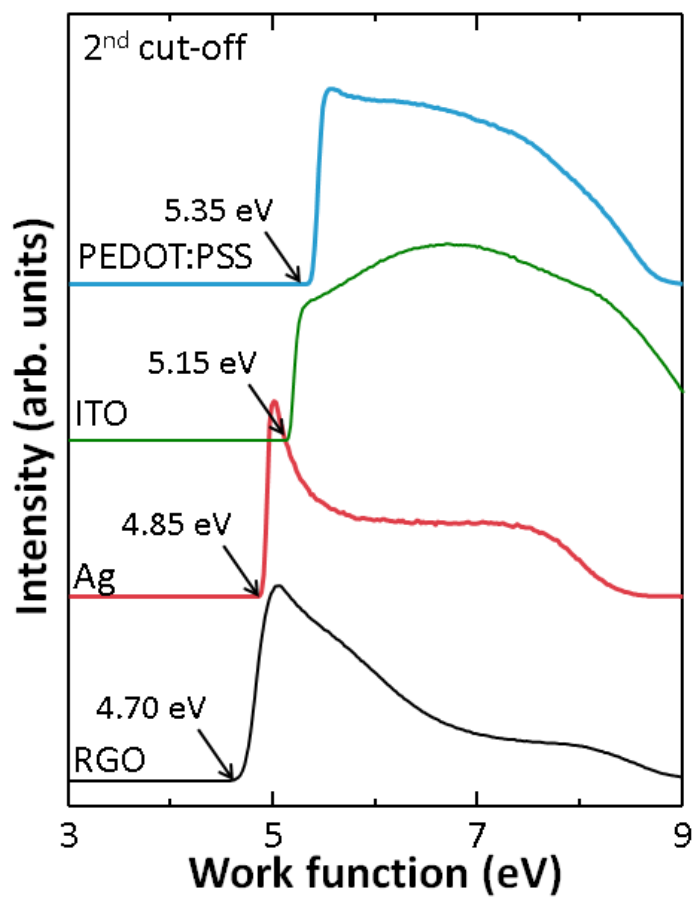
(b)



**Figure S1.** AFM height images of (a) annealed Ag and (b) annealed RGO samples. Scalebar: 1  $\mu\text{m}$



**Figure S2.** Raman spectra of as-printed GO, RGO, and annealed RGO samples.



**Figure S3.** Secondary cutoff spectra of printed S-D electrode materials using a UPS He I (21.2 eV) line. The arrows indicate the measured work function values.